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(54) **Method for erasing a memory cell**

(57) A method for erasing a non-volatile memory cell array, the method including applying an erase pulse to at least one bit of at least one memory cell of the array,

erase verifying the at least one bit with a first erase verify level, and if the bit has passed the first erase verify level, applying at least one more erase pulse to the at least one bit.

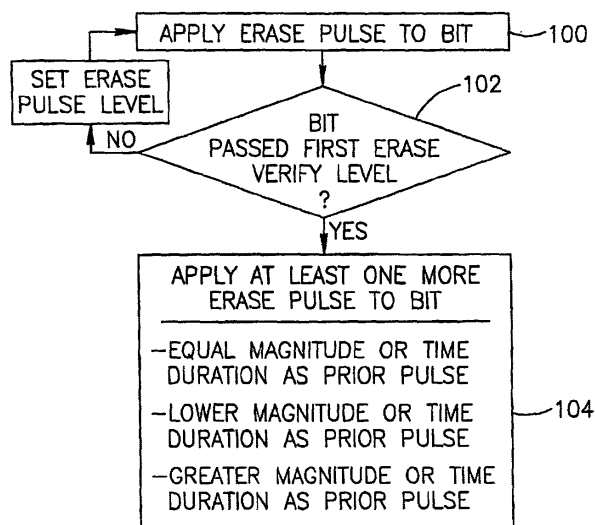


FIG.2

EP 1 306 855 A8